



# Bipolar PNP Bare Die – BTP6134

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## Part Description

The BTP6134 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6134

## Key Parameters:

- VCBO = -40V
- VCEO = -32V
- VEBO = -5V
- hFE = 82-433 @ VCE = -3V, IC = -0.5A
- VCE(Sat) = -0.8V @ IC = -2A, IB = -200mA
- fT = 100 MHz @ VCE = -5V, IE = 0A
- COBO = 50pF @ VCB = -10V

## Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SB1010

## Die Size (Unawn)

1020 $\mu$ m X 1020 $\mu$ m, 40 Mils X 40 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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